

## Linear Combination of Atomic Orbitals (LCAO) Form Molecular Orbitals (MO) = Hybridization

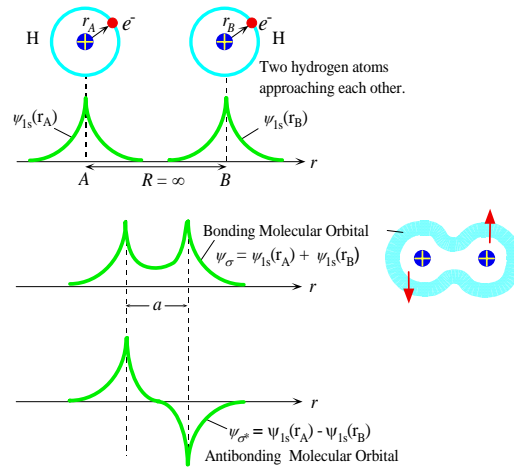


Fig. 4.1: Formation of molecular orbitals, bonding and antibonding ( $\psi_\sigma$  and  $\psi_{\sigma^*}$ ) when two H atoms approach each other. The two electrons pair their spins and occupy the bonding orbital  $\psi_\sigma$ .

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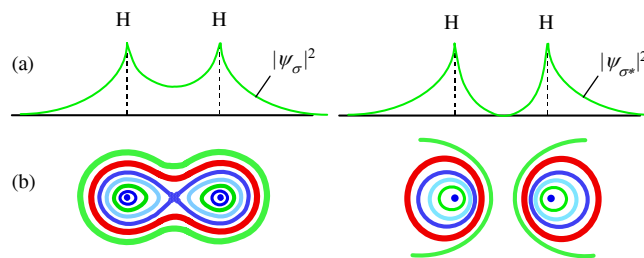


Fig. 4.2: (a) Electron probability distributions for bonding and antibonding orbitals,  $\psi_\sigma$  and  $\psi_{\sigma^*}$ . (b) Lines represent contours of constant probability (darker lines represent greater relative probability).

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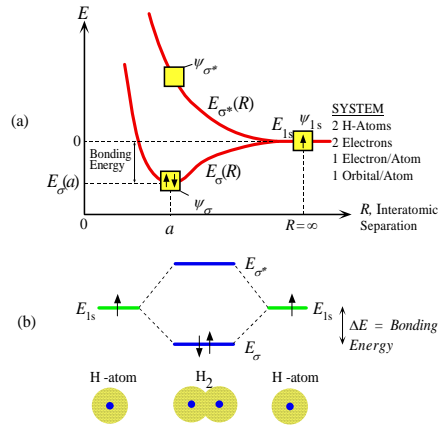


Fig. 4.3: Electron energy in the system comprising two hydrogen atoms. (a) Energy of  $\psi_\sigma$  and  $\psi_{\sigma^*}$  vs. the interatomic separation,  $R$ . (b) Schematic diagram showing the changes in the electron energy as two isolated H atoms, far left and far right, come to form a hydrogen molecule.

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## HF – SP Hybridization

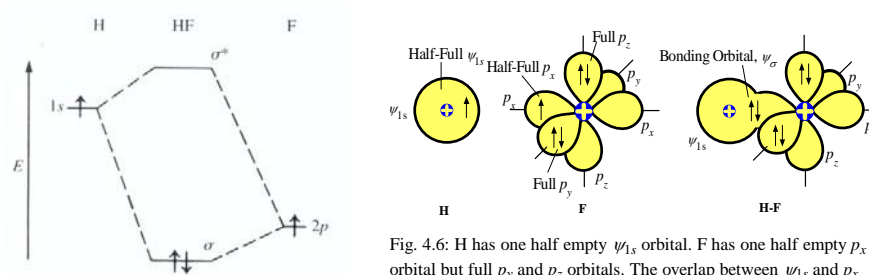


Figure 9.42  
A partial molecular orbital energy-level diagram for the HF molecule. The bonding can be accounted for in terms of MOs formed from a fluorine  $2p$  and a hydrogen  $1s$  orbital. Note that bonding occurs because the two electrons have lower energy in the HF molecule than they do in the free hydrogen and fluorine atoms.

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# Isolated Silicon

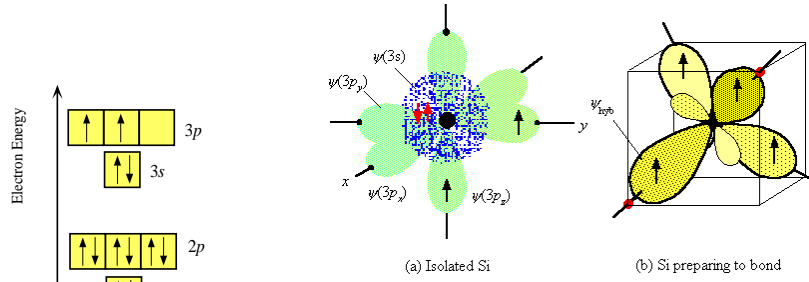


Fig. 4.15: The electronic structure of Si.

Fig. 4.16: (a) Si is in Group IV in the Periodic Table. An isolated Si atom has 2 electrons in the 3s and 2 electrons in the 3p orbitals. (b) When Si is about to bond, the one 3s-orbital and the three 3p-orbitals become perturbed and mixed to form four hybridized orbitals,  $\psi_{hyb}$ , called  $sp^3$  orbitals which are directed towards the corners of a tetrahedron. The  $\psi_{hyb}$  orbital has a large major lobe and a small back lobe. Each  $\psi_{hyb}$  orbital takes one of the four valence electrons.

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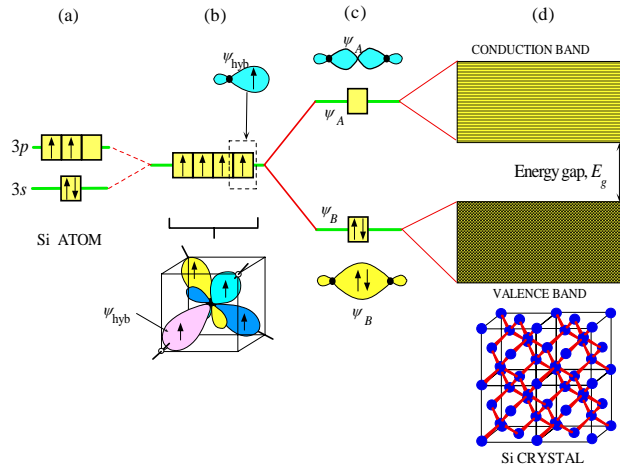


Fig. 4.17: (a) Formation of energy bands in the Si crystal first involves hybridization of 3s and 3p orbitals to four identical  $\psi_{hyb}$  orbitals which make  $109.5^\circ$  with each other as shown in (b). (c)  $\psi_{hyb}$  orbitals on two neighboring Si atoms can overlap to form  $\psi_B$  or  $\psi_A$ . The first is a bonding orbital (full) and the second is an antibonding orbital (empty). In the crystal  $\psi_B$  overlap to give the valence band (full) and  $\psi_A$  overlap to give the conduction band (empty).

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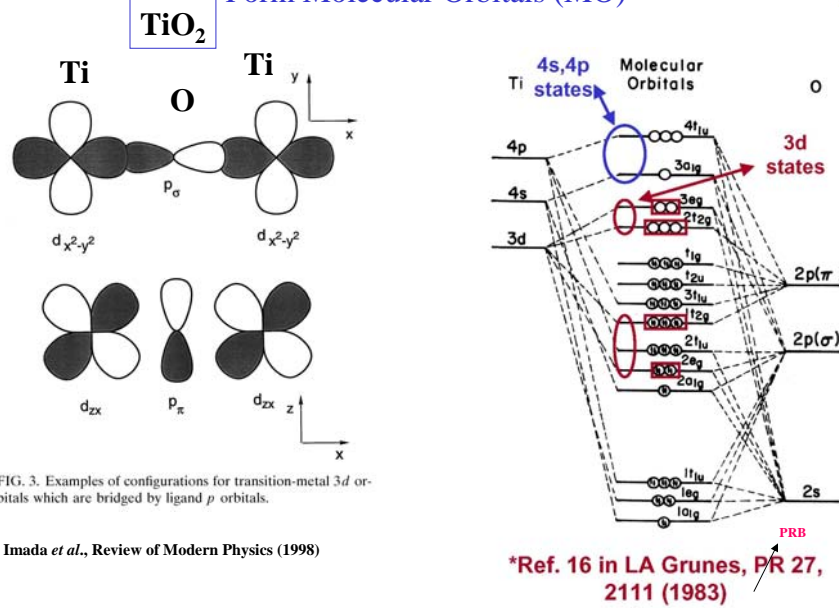
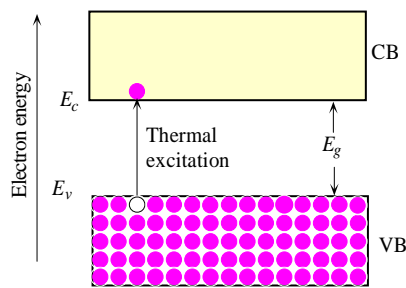


FIG. 3. Examples of configurations for transition-metal 3d orbitals which are bridged by ligand p orbitals.

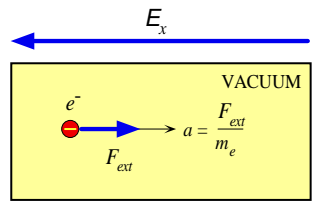
Imada *et al.*, Review of Modern Physics (1998)

Lucovsky, SEMATECH High-k Workshop, 2004

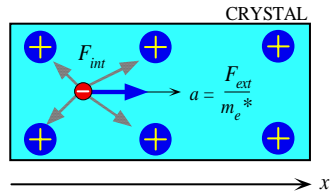


**Fig. 4.18:** Energy band diagram of a semiconductor. CB is the conduction band and VB is the valence band. At 0 K, the VB is full with all the valence electrons.

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(a)



(b)

Fig. 4.19: (a) An external force  $F_{ext}$  applied to an electron in vacuum results in an acceleration  $a_{vac} = F_{ext} / m_e$ . (b) An external force  $F_{ext}$  applied to an electron in a crystal results in an acceleration  $a_{cryst} = F_{ext} / m_e^*$ . ( $E_x$  is the electric field.)

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